Title (en)

SEMICONDUCTOR PROCESSING SILICA SOOT ABRASIVE SLURRY METHOD FOR INTEGRATED CIRCUIT MICROELECTRONICS

Title (de)

SCHLEIFMITTEL AUF BASIS VON SILIKA FÜR DIE BEARBEITUNG VON HALBLEITERSCHEIBEN

Title (fr)

MICRO-ELECTRONIQUE A CIRCUIT INTEGRES : TECHNIQUE DE TRAITEMENT DE SEMI-CONDUCTEURS AU MOYEN D'UNE SUSPENSION ABRASIVE A BASE DE SUIE DE SILICE

Publication

EP 1238417 A1 20020911 (EN)

Application

EP 00982198 A 20001122

Priority

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- US 16712199 P 19991123

Abstract (en)

[origin: WO0139260A1] The invention utilizes colloidal silica soot (62) in a semiconductor process for chemical-mechanical planarizing a semiconductor integrated circuit workpiece (24) with a slurry (60). The particulate abrasive agent colloidal solid sphere fused silica soot (62) provides a beneficial CMP slurry/process for semiconductor device manufacturing compared to standard semiconductor CMP slurries with conventional colloidal sol-gel or fumed silica.

IPC 1-7

H01L 21/302; H01L 21/461

IPC 8 full level

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